**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| Applicant: | Leonard Forbes et al. | Examiner: Pamela E. Perkins |
| Serial No.: | 10/623,788 | Group Art Unit: 2822 |
| Filed: | July 21, 2003 | Docket: 1303.109US1 |
| Title: | STRAINED SEMICONDUCTOR BY FULL WAFER BONDING | |

## COMMUNICATION CONCERNING RELATED APPLICATIONS

**MS AF**
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

| Serial/Patent No. | Filing Date/Issue Date | Attorney Docket | Title |
|---|---|---|---|
| 10/052,952<br>6,898,362 | January 17, 2002 | 1303.034US1 | THREE-DIMENSIONAL PHOTONIC CRYSTAL WAVEGUIDE STRUCTURE AND METHOD |
| 10/382,246 | March 5, 2003 | 1303.086US1 | CELLULAR MATERIALS FORMED USING SURFACE TRANSFORMATION |
| 10/379,749<br>7,198,974 | March 5, 2003 | 1303.089US1 | MICRO-MECHANICALLY STRAINED SEMICONDUCTOR FILM |
| 10/425,797<br>7,041,575 | April 29, 2003 | 1303.093US1 | LOCALIZED STRAINED SEMICONDUCTOR ON INSULATOR |
| 10/431,134<br>6,987,037 | May 7, 2003 | 1303.094US1 | STRAINED Si/SiGe STRUCTURES BY ION IMPLANTATION |
| 10/425,484<br>7,220,656 | April 29, 2003 | 1303.095US1 | STRAINED SEMICONDUCTOR BY WAFER BONDING WITH MISORIENTATION |
| 10/443,355<br>7,008,854 | May 21, 2003 | 1303.098US1 | SILICON OXYCARBIDE SUBSTRATES FOR BONDED SILICON ON INSULATOR |
| 10/443,340 | May 21, 2003 | 1303.099US1 | ULTRA-THIN SEMICONDUCTORS BONDED ON GLASS SUBSTRATES |
| 10/431,137<br>7,115,480 | May 7, 2003 | 1303.100US1 | MICROMECHANICAL STRAINED SEMICONDUCTOR BY WAFER BONDING |
| 10/634,174<br>7,153,753 | August 5, 2003 | 1303.102US1 | STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME |

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| 10/443,337 | May 21, 2003 | 1303.103US1 | GETTERING OF SILICON ON INSULATOR USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS |
| 10/623,794<br>6,929,984 | July 21, 2003 | 1303.108US1 | GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION |
| 10/931,554<br>7,023,051 | August 31, 2004 | 1303.093US2 | LOCALIZED STRAINED SEMICONDUCTOR ON INSULATOR |
| 10/931,749<br>7,084,429 | August 31, 2004 | 1303.095US2 | STRAINED SEMICONDUCTOR BY WAFER BONDING WITH MISORIENTATION |
| 10/931,344 | August 31, 2004 | 1303.108US2 | GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION |
| 10/931,553 | August 31, 2004 | 1303.099US2 | ULTRA-THIN SEMICONDUCTORS BONDED ON GLASS SUBSTRATES |
| 10/931,580<br>7,045,874 | August 31, 2004 | 1303.100US2 | MICROMECHANICAL STRAINED SEMICONDUCTOR BY WAFER BONDING |
| 10/979,994 | November 3, 2004 | 1303.102US2 | STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME |
| 11/005,712<br>7,054532 | December 7, 2004 | 1303.034US2 | THREE-DIMENSIONAL PHOTONIC CRYSTAL WAVEGUIDE STRUCTURE AND METHOD |
| 11/210,927<br>7,202530 | August 24, 2005 | 1303.089US2 | MICRO-MECHANICALLY STRAINED SEMICONDUCTOR FILM |
| 11/167,894 | June 27, 2005 | 1303.108US3 | GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION |
| 11/210,373 | August 24, 2005 | 1303.094US2 | STRAINED Si/SiGe STRUCTURES BY ION IMPLANTATION |
| 11/214,495 | August 29, 2005 | 1303.098US2 | SEMICONDUCTOR ON INSULATOR STRUCTURE |
| 11/318124 | December 23, 2005 | 1303.095US3 | STRAINED SEMICONDUCTOR BY WAFER BONDING WITH MISORIENTATION |
| 11/497,632 | August 2, 2006 | 1303.186US1 | STRAINED SEMICONDUCTOR, DEVICES AND SYSTEMS AND METHODS OF FORMATION |

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| 11/353,406 | February 14, 2006 | 1303.086US2 | CELLULAR MATERIALS FORMED USING SURFACE TRANSFORMATION |
| 11/432,578 | May 11, 2006 | 1303.100US3 | MICROMECHANICAL STRAINED SEMICONDUCTOR BY WAFER BONDING |
| 11/475,798 | June 27, 2006 | 1303.109US2 | STRAINED SEMICONDUCTOR BY FULL WAFER BONDING |
| 11/493,128 | July 26, 2006 | 1303.099US3 | SEMICONDUCTORS BONDED ON GLASS SUBSTRATES |
| 11/460,391 | July 27, 2006 | 1303.103US2 | GETTERING OF SILICON ON INSULATOR USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS |
| 11/494,319 | July 27, 2006 | 1303.102US3 | STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME |
| 11/707,214 | February 13, 2007 | 1303.089US3 | MICRO-MECHANICALLY STRAINED SEMICONDUCTOR FILM |
| 09/855,532 | May 16, 2001 | | METHOD OF FORMING MIRRORS BY SURFACE TRANSFORMATION OF EMPTY SPACES IN SOLID STATE MATERIALS |
| 10/118,350 | April 14, 2004 | | METHOD OF FORMING SPATIAL REGIONS OF A SECOND MATERIAL IN A FIRST MATERIAL |
| 10/093,332 | April 14, 2004 | | METHOD AND APPARATUS FOR PACKAGING SEMICONDUCTOR DEVICES |

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being filed using the USPTO's electronic filing system EFS-Web,and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 29 day of May, 2007.

LISA PESONEN
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Signature